

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

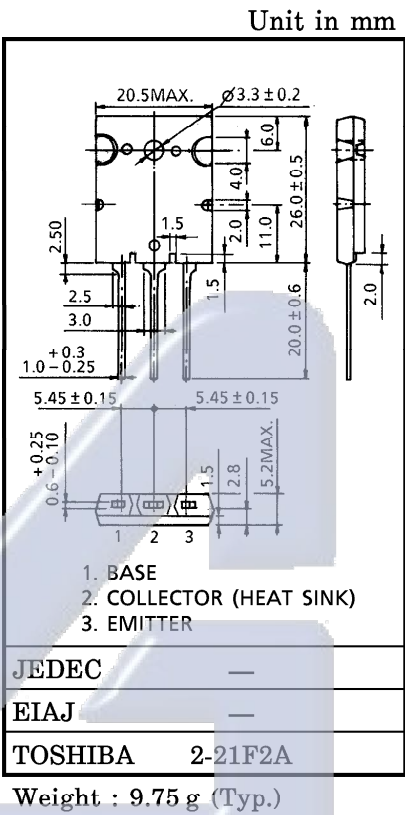
2SC5570

HORIZONTAL DEFLECTION OUTPUT FOR SUPER HIGH RESOLUTION
DISPLAY, COLOR TV
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f(2) = 0.1\text{ }\mu\text{s (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1700	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	28	A
	Pulse	I_{CP}	56	A
Base Current		I_B	14	A
Collector Power Dissipation (Tc = 25°C)		P_C	220	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



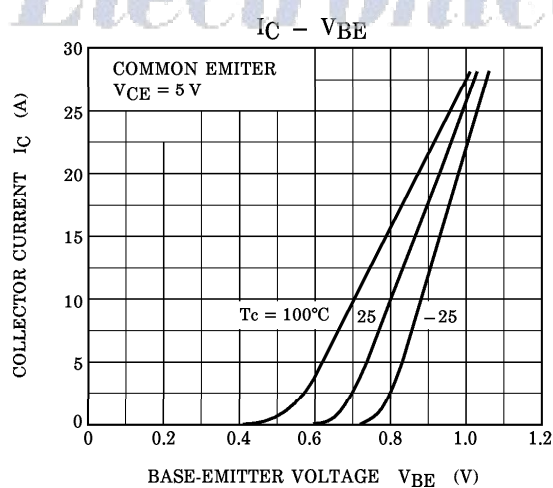
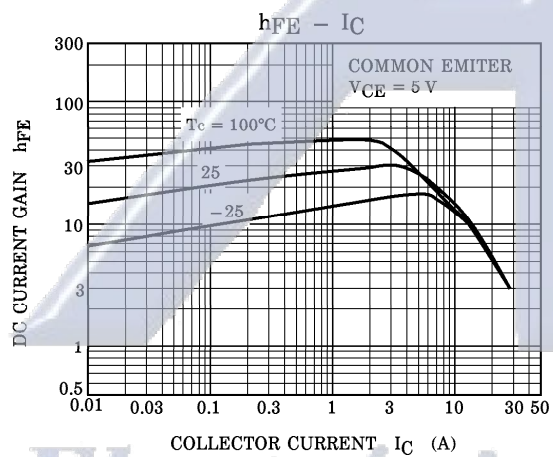
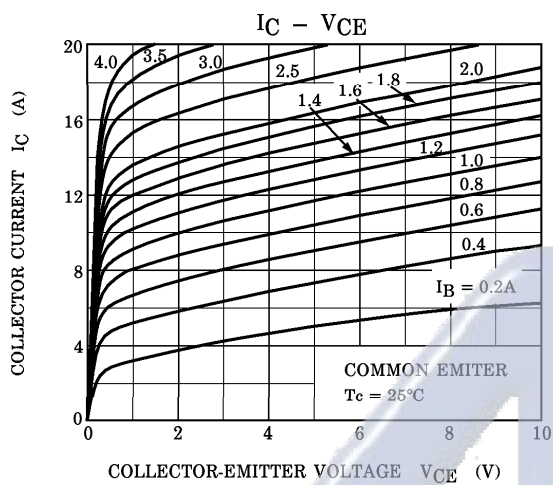
Electrónica S.A. de C.V.

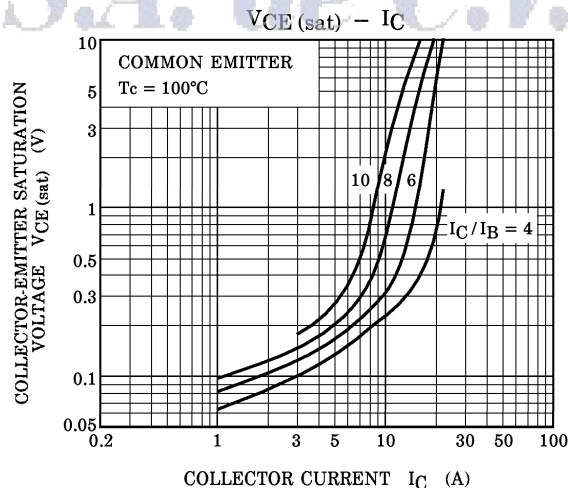
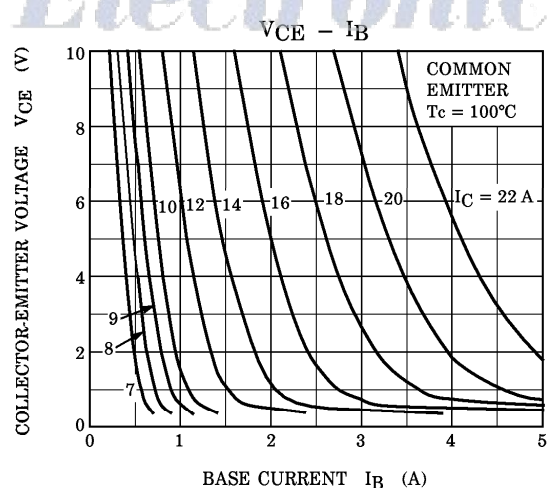
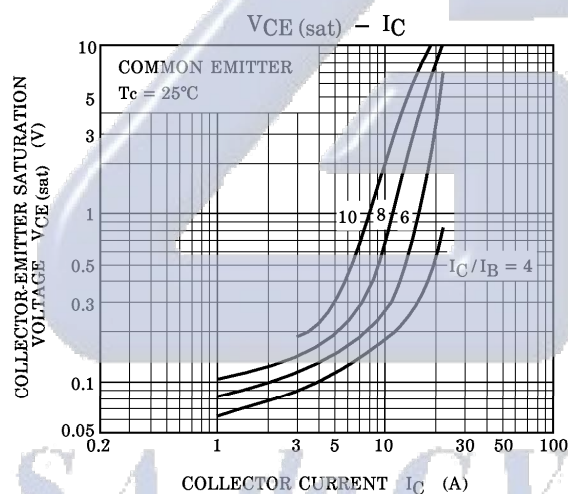
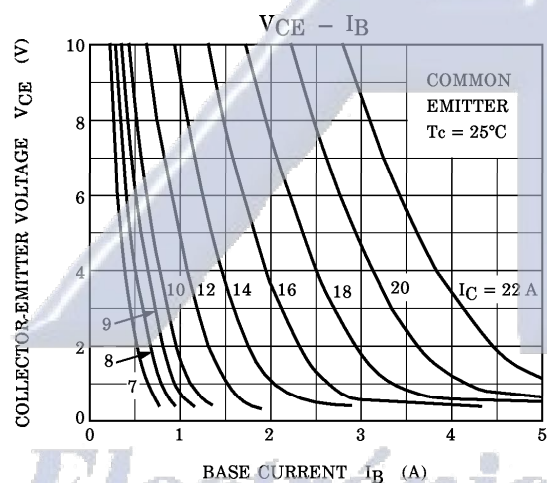
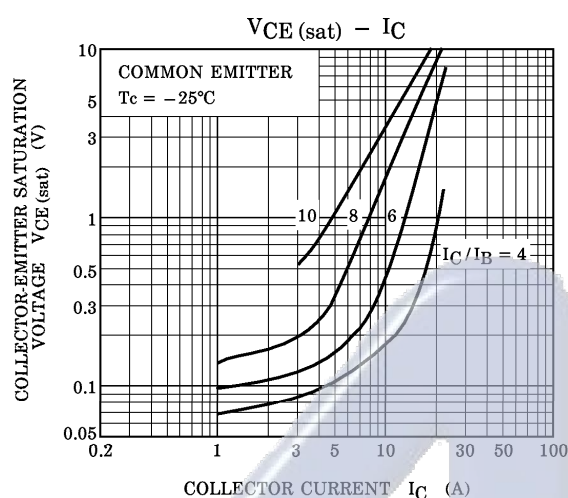
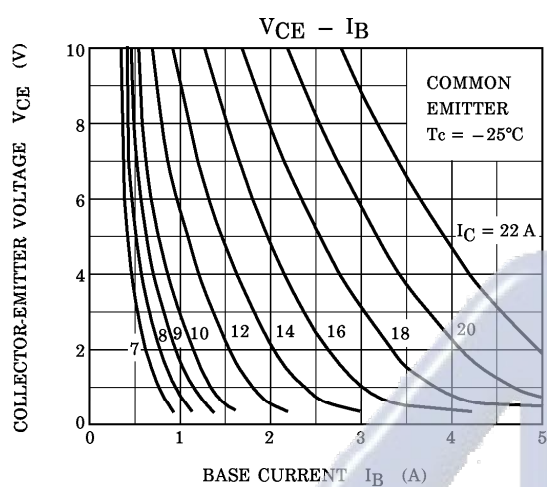
TOSHIBA**2SC5570**

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1700\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	800	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	22	—	48	
		$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 8\text{ A}$	12.5	—	25	
		$h_{FE(3)}$	$V_{CE} = 5\text{ V}, I_C = 22\text{ A}$	4.5	—	7.5	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 22\text{ A}, I_B = 5.5\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 22\text{ A}, I_B = 5.5\text{ A}$	—	1.0	1.5	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	470	—	pF
Switching Time	Storage Time	$t_{stg(1)}$	$I_{CP} = 10\text{ A}, I_{B1}(\text{end}) = 1.4\text{ A}$	—	2.6	3.0	μs
	Fall Time	$t_f(1)$	$f_H = 64\text{ kHz}$	—	0.2	0.3	
	Storage Time	$t_{stg(2)}$	$I_{CP} = 8\text{ A}, I_{B1}(\text{end}) = 1.2\text{ A}$	—	1.4	1.6	μs
	Fall Time	$t_f(2)$	$f_H = 130\text{ kHz}$	—	0.10	0.15	

Electrónica S.A. de C.V.

TOSHIBA**2SC5570**

TOSHIBA**2SC5570**

TOSHIBA**2SC5570**